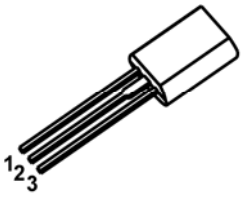
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92MOD Plastic-Encapsulate Transistors

2SC2229 TRANSISTOR (NPN)

TO – 92MOD

1. EMITTER
2. COLLECTOR
3. BASE



FEATURES

- High Breakdown Voltage
- High Transition Frequency

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	150	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	50	mA
P_C	Collector Power Dissipation	800	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	156	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

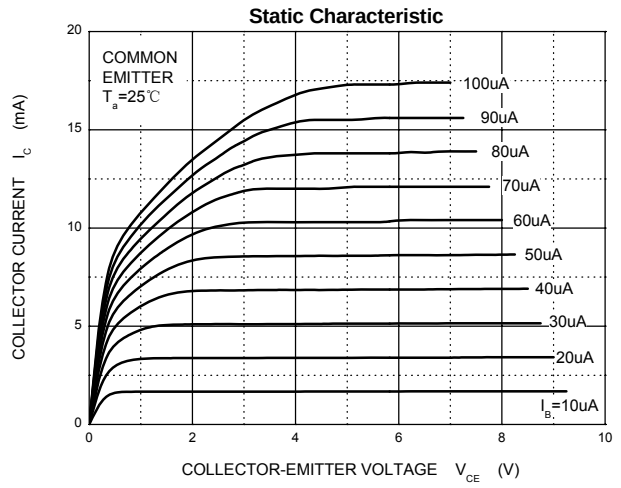
ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

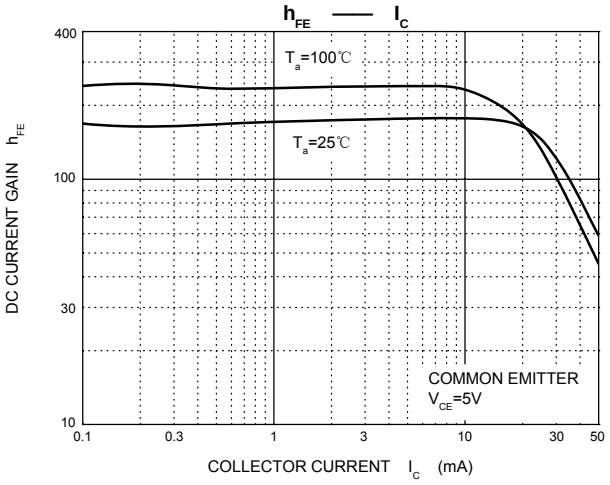
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 100μA,I_E=0	200			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	150			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA,I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=200V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V,I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=5V, I_C=10mA	70		240	
	$h_{FE(2)}$	V_{CE}=5V, I_C=1mA	50			
	$h_{FE(3)}$	V_{CE}=5V, I_C=50mA	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=10mA,I_B=1mA			0.5	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C=10mA,I_B=1mA			1	V
Transition frequency	f_T	V_{CE}=30V,I_C=10mA	80			MHz

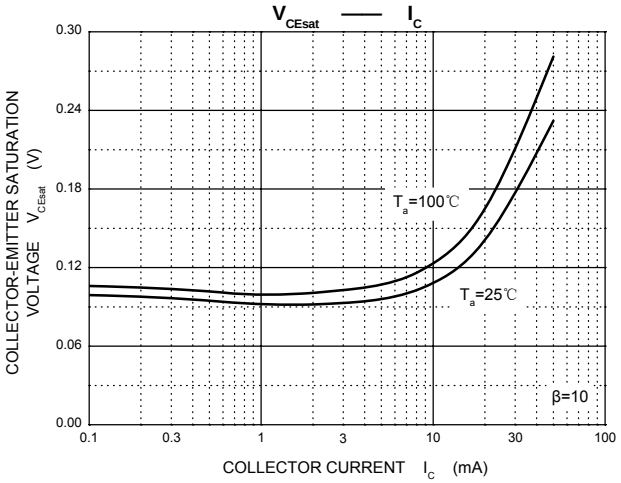
CLASSIFICATION OF $h_{FE(1)}$

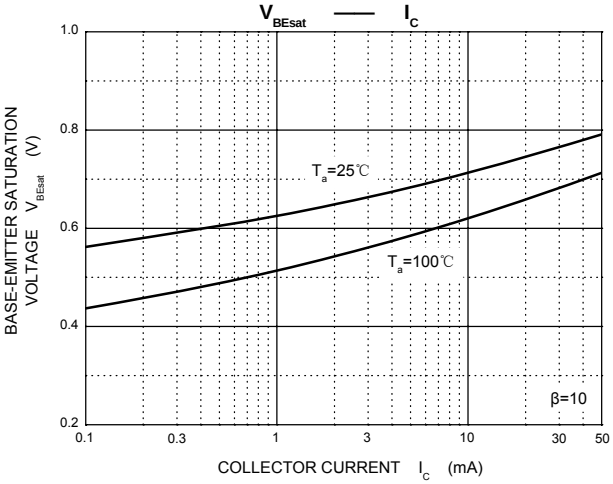
RANK	O	Y
RANGE	70-140	120-240

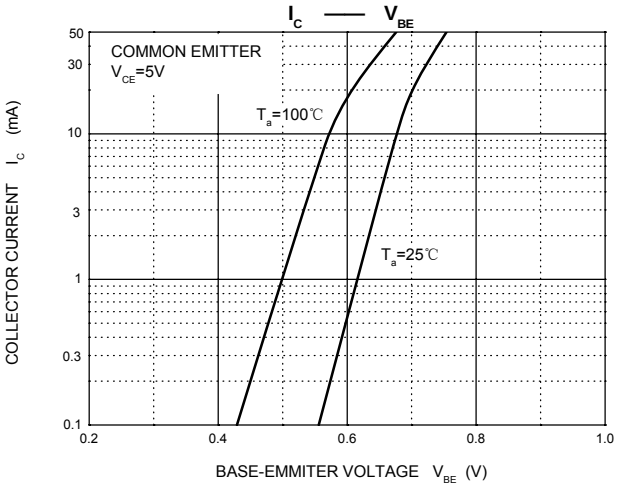
Typical Characterisitics 2SC2229

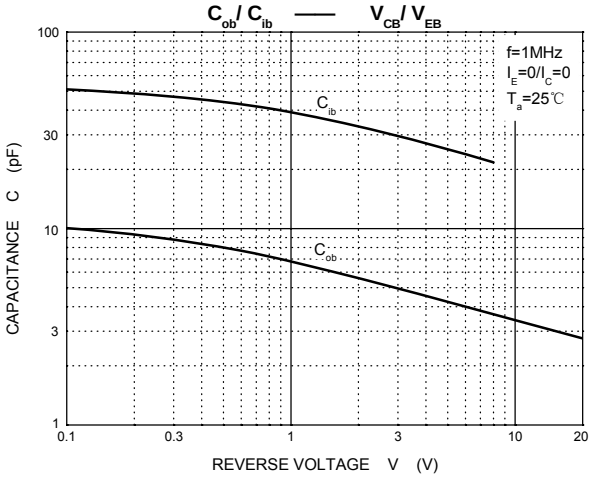


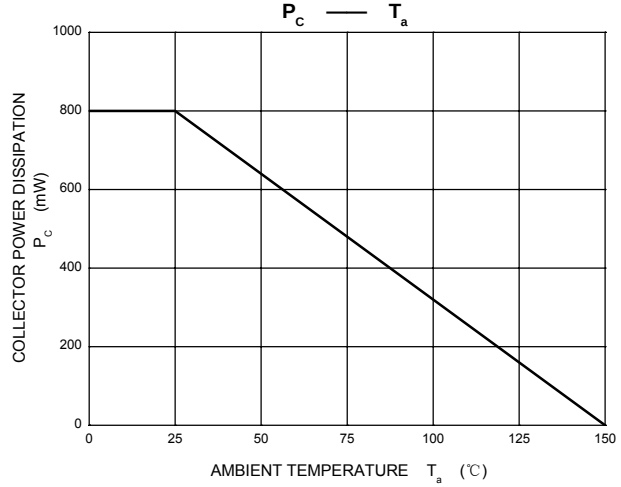












A,Dec,2010